eer

Notice of Allowability	Application No.	Applicant(s)
	10/511,212	PEAKE, STEVEN T
	Examiner	Art Unit
	Eugene Lee	2815
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.		
1. This communication is responsive to 4/12/07.		
2. The allowed claim(s) is/are <u>1-15</u> .		
<ul> <li>3. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some* c) None of the:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No.</li> <li>3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* Certified copies not received:</li> </ul>		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.  THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		
4. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.		
<ul> <li>5. CORRECTED DRAWINGS ( as "replacement sheets") must be submitted.</li> <li>(a) including changes required by the Notice of Draftsperson's Patent Drawing Review ( PTO-948) attached</li> <li>1) hereto or 2) to Paper No./Mail Date</li> <li>(b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date</li> <li>Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).</li> </ul>		
6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.		
<ul> <li>Attachment(s)</li> <li>1. ☑ Notice of References Cited (PTO-892)</li> <li>2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)</li> <li>3. ☐ Information Disclosure Statements (PTO/SB/08),</li></ul>	5. ☐ Notice of Informal P 6. ☐ Interview Summary Paper No./Mail Dat 7. ☐ Examiner's Amendn 8. ☑ Examiner's Stateme 9. ☐ Other	(PTO-413), enent/Comment ent of Reasons for Allowance
		PRIMERY EXAMINER

Art Unit: 2815

## **DETAILED ACTION**

## Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 4/12/07 has been entered.

## Allowable Subject Matter

2. Claims 1 thru 15 are allowed. The following is an examiner's statement of reasons for allowance: The references of record, either singularly or in combination, do not teach or suggest at least a vertical power transistor trench-gate semiconductor device comprising a semiconductor body, wherein ruggedness regions are provided which are localized regions of the second conductivity type but which are more heavily doped than the channel-accommodating regions and which extend into the drain region, wherein the source regions and the ruggedness regions extend to a source contact surface of the semiconductor body as alternating stripe areas having a width perpendicular to and fully between each of two adjacent parallel stripe trench-gates, and wherein the device is characterized by the ruggedness regions being more heavily doped than the source regions.

Regarding claim 15, the references of record, either singularly or in combination, do not teach or suggest at least a vertical power transistor trench-gate semiconductor device comprising a semiconductor body, wherein ruggedness regions are provided which are localized regions of

Art Unit: 2815

the second conductivity type buy which are more heavily doped than the channelaccommodating regions and which extend into the drain region, wherein the trench-gates are parallel stripes, wherein the source regions and the ruggedness regions extend to a source contact surface of the semiconductor body as alternating stripe areas having a width perpendicular to and fully between each of two adjacent parallel stripe trench-gates, and wherein the device is characterized by the ruggedness regions being more heavily doped than the source regions, and wherein the length of the ruggedness regions is less than the length of the source regions, and wherein a distance between two immediately adjacent channel-accommodating regions equals the width of the source regions.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## INFORMATION ON HOW TO CONTACT THE USPTO

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Eugene Lee whose telephone number is 571-272-1733. The examiner can normally be reached on M-F 8-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Kenneth Parker can be reached on 571-272-2298. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 2815

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Eugene Lee

June 19, 2007